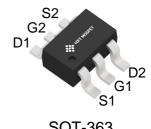


## **Description**

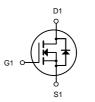
The HDMN601DWK7 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-363 (SC-70-6)

### **General Features**

 $V_{DS} = 60V I_D = 0.115 A$  $R_{DS(ON)} < 3\Omega@V_{GS}=10V$ 





## **Application**

Wireless charging

Boost driver

Brushless motor

**Dual N-Channel MOSFET** 

**Package Marking and Ordering Information** 

Product ID	Pack	Marking	Qty(PCS)
HDMN601DWK7	SOT-363(SC-70-6)	72K	3000

### Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	CDrain Current-Continuous	0.115	А
P <sub>D</sub>	Maximum Power Dissipation	0.15	W
ТЈ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	833	°C/W

### Dual N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA	60			V
Gate-threshold voltage *	$V_{th(GS)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA	1	1.6	2.5	V
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V			±80	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V			80	nA
Duein course on recistores *	R <sub>DS(on)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> =500mA		1.3	3	0
Drain-source on-resistance *		V <sub>GS</sub> =4.5V, I <sub>D</sub> =50mA		2	5	Ω
Forward transconductance *	g <sub>fs</sub>	V <sub>DS</sub> =10 V, I <sub>D</sub> =200mA	80			ms
Dusin serves on velters *	V <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			3.75	V
Drain-source on-voltage *		V <sub>GS</sub> =5V, I <sub>D</sub> =50mA			0.375	V
Diode forward voltage	$V_{SD}$	I <sub>S</sub> =115mA, V <sub>GS</sub> =0 V	0.55		1.2	V
Input capacitance **	C <sub>iss</sub>				50	
Output capacitance **	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz			25	pF
Reverse transfer capacitance **	C <sub>rss</sub>				5	

### **SWITCHING TIME**

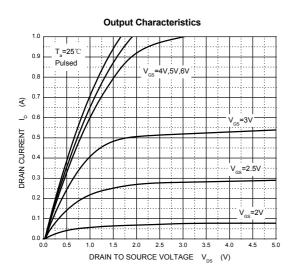
Turn-on time **	t <sub>d(on)</sub>	V <sub>DD</sub> =25 V, R <sub>L</sub> =50Ω		20	ns
Turn-off time **	$t_{d(off)}$	$I_D$ =500mA, $V_{GEN}$ =10 $V_{G}$ =25 $\Omega$		40	110

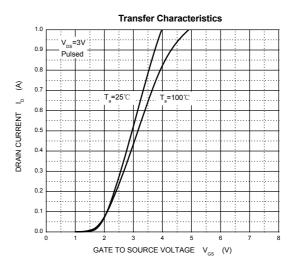
<sup>\*</sup> Pulse Test: Pulse width ≤300µs,duty cycle≤2%.

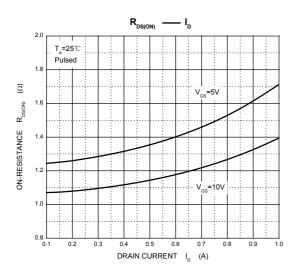
<sup>\*\*</sup> These parameters have no way to verify.

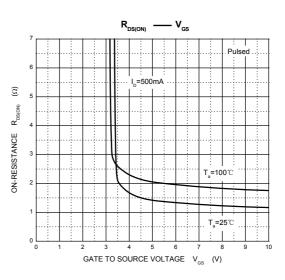


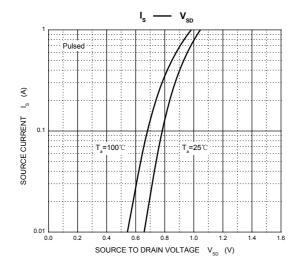
## **Typical Characteristics**

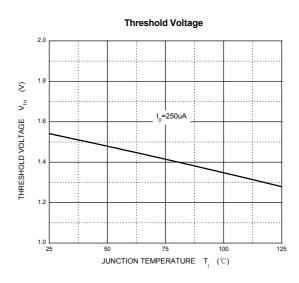






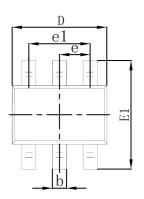


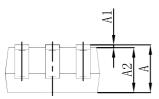


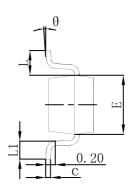




# SOT-363(SC-70-6) Package Outline Dimensions

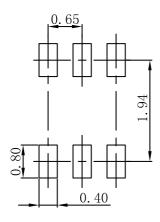






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525	REF	0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# SOT-363(SC-70-6) Suggested Pad Layout



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **Dual N-Channel Enhancement Mode MOSFET**

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